**Product data sheet** 

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DSN1010-3 (SOT8007) Surface-Mounted Device (SMD) package using Trench MOSFET technology.

### 2. Features and benefits

- · Low threshold voltage
- Very fast switching
- Ultra small package: 0.96 × 0.96 × 0.24 mm
- Trench MOSFET technology

### 3. Applications

- Relay driver
- · Battery management
- · Low-side load switch
- · Switching circuits

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	12	V
$V_{GS}$	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-	14	Α
Static chara	acteristics			<u>'</u>	'	'	
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}$		-	13.2	16	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), 4 layer copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



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## 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D
2	D	drain	1 2	
3	S	source	3	mbb076 S
			Transparent top view DSN1010-3 (SOT8007)	

## 6. Ordering information

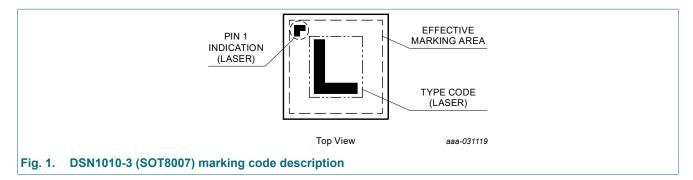
**Table 3. Ordering information** 

Type number	number Package					
	Name	Description	Version			
PMCA14UN	DSN1010-3	chip-scale package; 3 terminals; body 0.96 x 0.96 x 0.24 mm	SOT8007			

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PMCA14UN	L



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### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	12	V
V <sub>GS</sub>	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	14	Α
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	11	Α
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	7	Α
I <sub>DM</sub>	peak drain current	T <sub>amb</sub> = 25 °C; single pulse; t <sub>p</sub> ≤ 10 μs		-	44	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	1.2	W
			[1]	-	2.5	W
		T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	3.9	W
		T <sub>sp</sub> = 25 °C		-	31	W
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drai	n diode		'	'	-	
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	1.2	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), 4 layer copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), 4 layer copper, tin-plated and standard footprint.

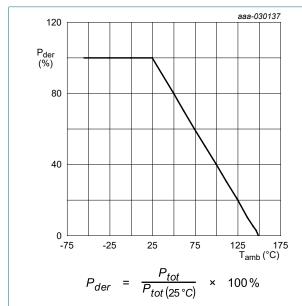


Fig. 2. Normalized total power dissipation as a function of ambient temperature

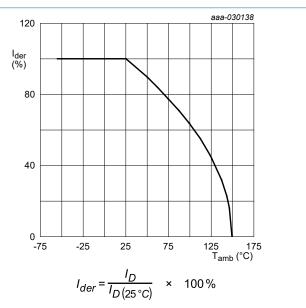


Fig. 3. Normalized continous drain current as a function of ambient temperature

### 12 V, N-channel Trench MOSFET

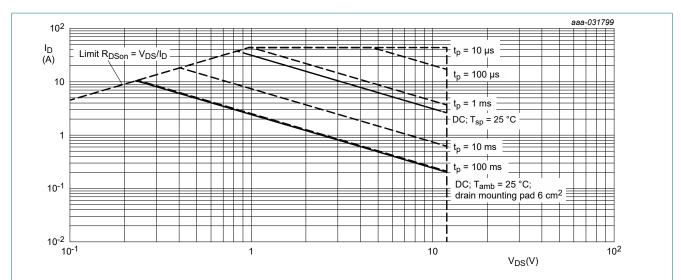


Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

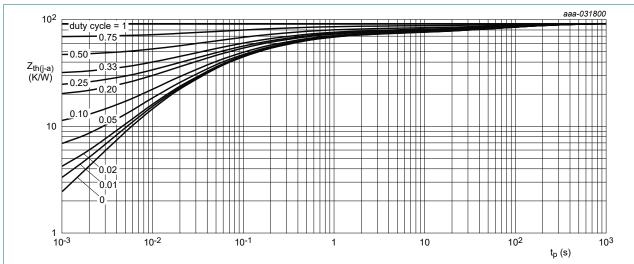
12 V, N-channel Trench MOSFET

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

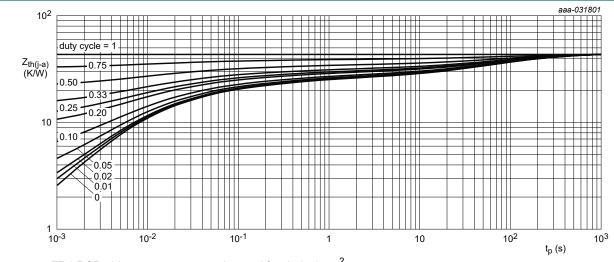
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from	in free air	[1]	-	92	106	K/W
	junction to ambient		[2]	-	43	50	K/W
		in free air; t ≤ 5 s	[2]	-	28	32	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	2	4	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), 4 layer copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), 4 layer copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



FR4 PCB, 4 layer copper, standard footprint

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 4 layer copper, mounting pad for drain 6 cm<sup>2</sup>

Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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## 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	12	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.4	0.6	0.9	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 9.6 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	13.2	16	mΩ
	resistance	$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A}; T_j = 150 \text{ °C}$	-	17	21	mΩ
		$V_{GS} = 3.3 \text{ V}; I_D = 5 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	14.2	17	mΩ
		$V_{GS} = 2.5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	16	21	mΩ
		V <sub>GS</sub> = 1.8 V; I <sub>D</sub> = 1 A; T <sub>j</sub> = 25 °C	-	22	35	mΩ
9fs	forward transconductance	$V_{DS} = 6 \text{ V}; I_D = 1 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	5.6	-	S
$R_G$	gate resistance	f = 1 MHz	-	1.5	-	Ω
Dynamic ch	naracteristics		'			
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = 6 \text{ V}; I_D = 5 \text{ A}; V_{GS} = 3.3 \text{ V};$	-	8	12	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	1.3	-	nC
$Q_{GD}$	gate-drain charge		-	3.2	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 6 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	855	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	257	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	237	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 6 \text{ V}; I_D = 5 \text{ A}; V_{GS} = 3.3 \text{ V};$	-	3	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	6	-	ns
t <sub>d(off)</sub>	turn-off delay time	]	-	16	-	ns
t <sub>f</sub>	fall time		-	11	-	ns
Source-drai	in diode		1		1	
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 1.2 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	0.7	1.2	V

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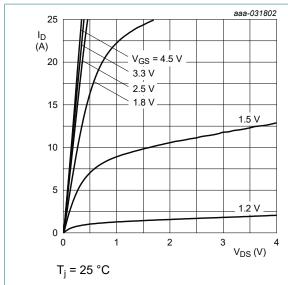


Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values

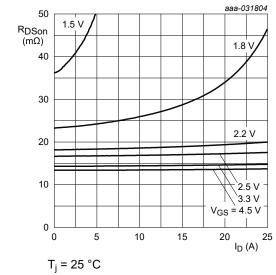
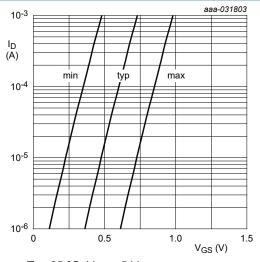


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values



 $T_j = 25 \,^{\circ}C; V_{DS} = 5 \,^{\circ}V$ 

Fig. 8. Subthreshold drain current as a function of gate-source voltage

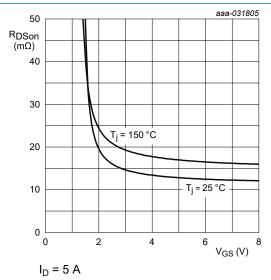


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

#### 12 V, N-channel Trench MOSFET

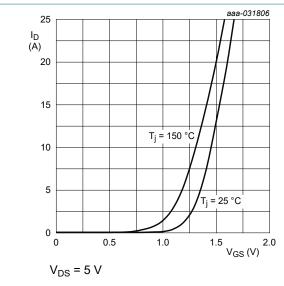


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

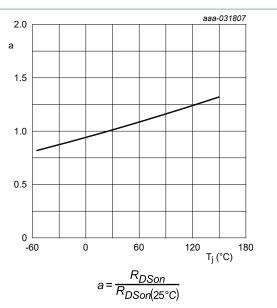


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

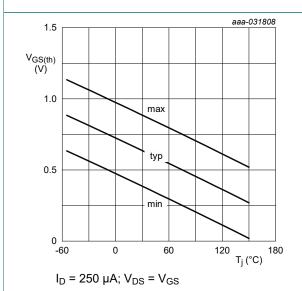


Fig. 13. Gate-source threshold voltage as a function of junction temperature

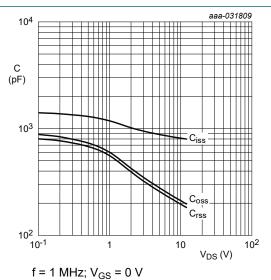


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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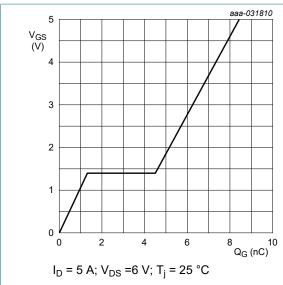


Fig. 15. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$ 

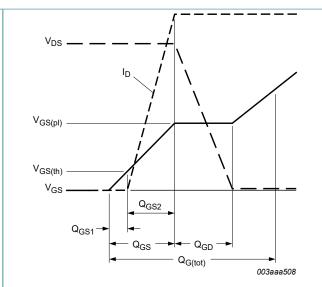


Fig. 16. Gate charge waveform definitions

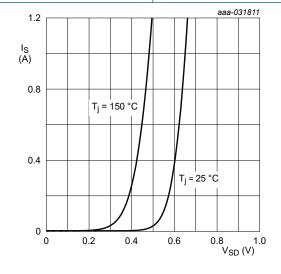
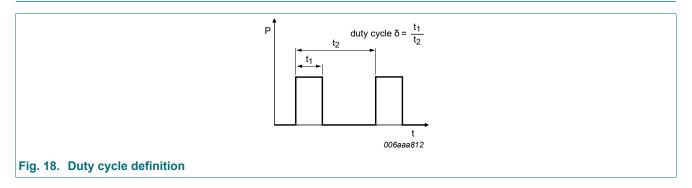


Fig. 17. Source current as a function of source-drain voltage; typical values

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## 11. Test information



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## 12. Package outline

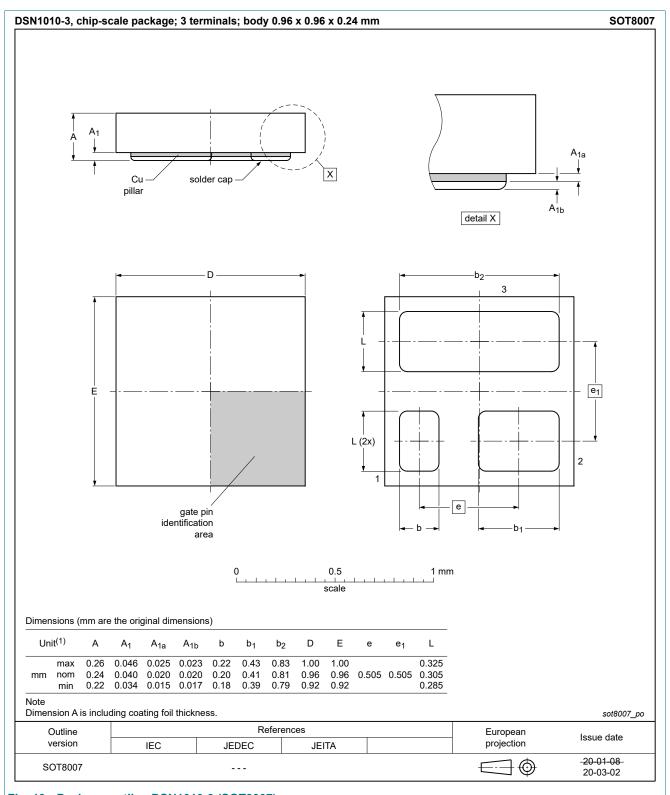
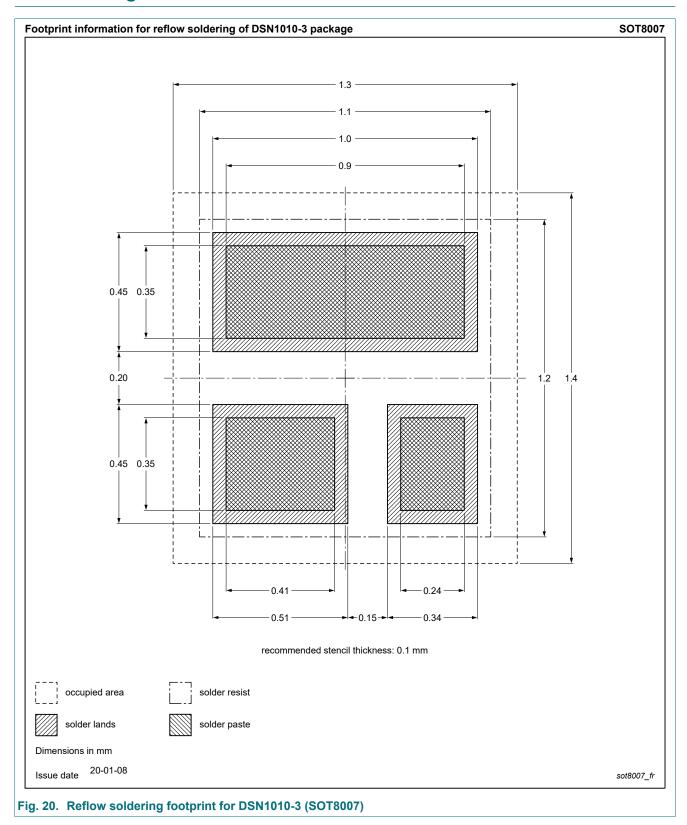


Fig. 19. Package outline DSN1010-3 (SOT8007)

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## 13. Soldering



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# 14. Revision history

### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMCA14UN v.1	20200806	Product data sheet	-	-

#### 12 V, N-channel Trench MOSFET

### 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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